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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Complete if Known		
			Application Number	10/706,737-Conf. #7548	
			Filing Date	November 12, 2003	
			First Named Inventor	Xiaojun Weng	
			Art Unit	2812	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	1	Attorney Docket Number	65306-0094

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
2	CA	44th Electronic Materials Conference Oral presentation entitled "Ion-Cut-Synthesis of Narrow Gap Nitride Nanostructures" by X. Weng, et al. dated June, 2002	
2	CB	2002 Spring Meeting of the Materials Research Society, Oral presentation entitled "Ion-Cut-Synthesis of Narrow Gap Nitride Alloys" by X. Weng, et al., dated April, 2002	
2	CC	Journal of Vacuum Science and Technology B, publication entitled "Formation and Blistering of GaAsN Nanostructure Layers" by X. Weng, et al. dated May/June, 2004 issue.	

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Examiner Signature	<i>[Signature]</i>	Date Considered	6/24/05
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